# MOSFET – N-Channel, SOT-23 500 mA, 60 V

## Features

- NVBF Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	Vdc
Drain-Gate Voltage	V <sub>DGS</sub>	60	Vdc
Gate–Source Voltage – Continuous – Non–repetitive (t <sub>p</sub> ≤ 50 μs)	V <sub>GS</sub> V <sub>GSM</sub>	±20 ±40	Vdc Vpk
Drain Current – Continuous – Pulsed	I <sub>D</sub> I <sub>DM</sub>	0.5 0.8	Adc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Total Device Dissipation FR- 5 Board (Note 1.) T <sub>A</sub> = 25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	– 55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR–5 = 1.0  $\times$  0.75  $\times$  0.062 in.



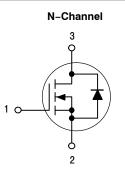
# **ON Semiconductor®**

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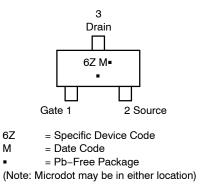
# 500 mA, 60 V

 $R_{DS(on)} = 5 \Omega$ 





### MARKING DIAGRAM & PIN ASSIGNMENT



### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS	3		•		-
Drain-Source Breakdowr	n Voltage (V <sub>GS</sub> = 0, I <sub>D</sub> = 100 μA)	V <sub>(BR)DSS</sub>	60	-	Vdc
Gate-Body Leakage Cur	rent, Forward (V <sub>GSF</sub> = 15 Vdc, V <sub>DS</sub> = 0)	I <sub>GSS</sub>	-	10	nAdc
ON CHARACTERISTICS	(Note 1)				
Gate Threshold Voltage (	$V_{DS} = V_{GS}$ , $I_D = 1.0$ mA)	V <sub>GS(th)</sub>	0.8	3.0	Vdc
Static Drain-Source On-Resistance ( $V_{GS}$ = 10 Vdc, $I_D$ = 200 mA)		r <sub>DS(on)</sub>	-	5.0	Ω
On–State Drain Current ( $V_{DS}$ = 25 Vdc, $V_{GS}$ = 0)		I <sub>D(off)</sub>	-	0.5	μA
DYNAMIC CHARACTERI	STICS				
Input Capacitance (V <sub>DS</sub> = 10 Vdc, V <sub>GS</sub> = 0 V, f = 1.0 MHz)		C <sub>iss</sub>	-	60	pF
SWITCHING CHARACTE	RISTICS (Note 1)	-	•	-	-
Turn-On Delay Time	(V <sub>DD</sub> = 25 Vdc, I <sub>D</sub> = 500 mA, R <sub>gen</sub> = 50 $\Omega$ )	t <sub>d(on)</sub>	-	10	ns
Turn-Off Delay Time	Figure 1	t <sub>d(off)</sub>	-	10	1

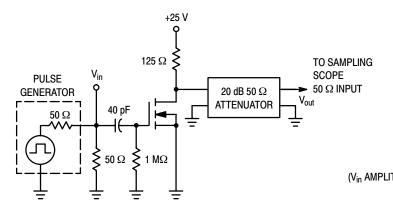
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

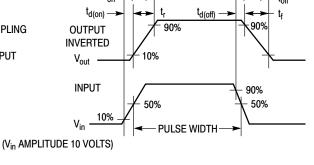
1. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBF170LT1G	SOT-23 (TO-236) (Pb-Free)	3000 / Tape & Reel
MMBF170LT3G	SOT-23 (TO-236) (Pb-Free)	10000 / Tape & Reel
NVBF170LT1G*	SOT-23 (TO-236) (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

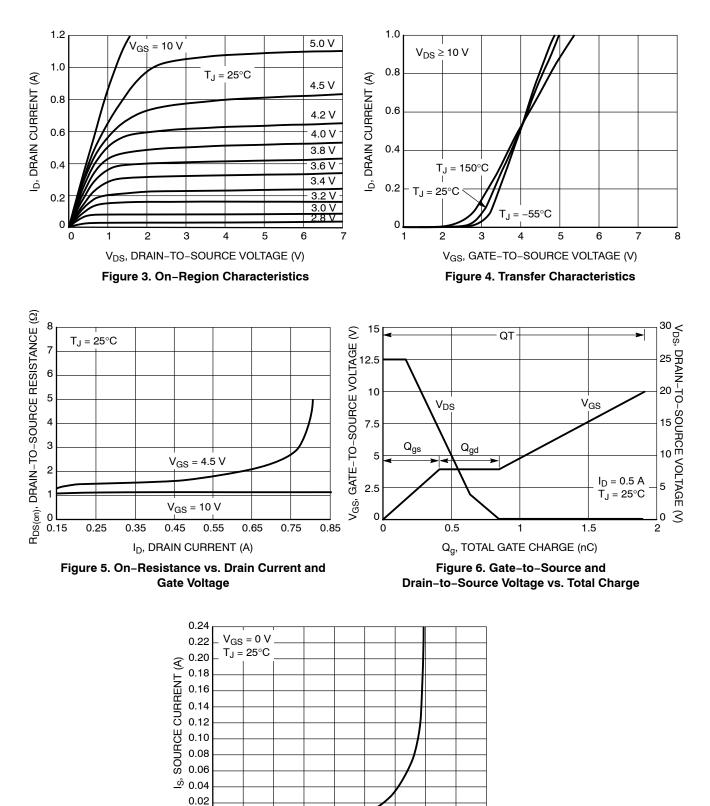








# **TYPICAL ELECTRICAL CHARACTERISTICS**



0.6

V<sub>SD</sub>, SOURCE-TO-DRAIN VOLTAGE (V) Figure 7. Diode Forward Voltage vs. Current

0.7

0.8

0.9

1.0

0

0.1

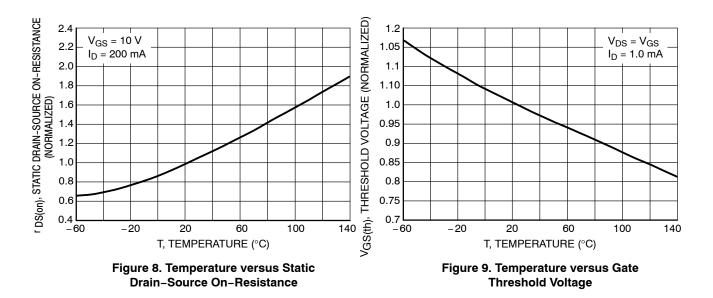
0.2

0.3

0.4

0.5

# **TYPICAL ELECTRICAL CHARACTERISTICS**



# semi



#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318**

**ISSUE AU** 

DATE 14 AUG 2024













XXX = Specific Device Code М = Date Code

= Pb-Free Package .

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MILLIMETERS				
DIM	MIN	NOM	МАХ	
А	0.89	1.00	1.11	
A1	0.01	0.06	0.10	
b	0.37	0.44	0.50	
с	0.08	0.14	0.20	
D	2.80	2.90	3.04	
E	1.20	1.30	1.40	
е	1.78	1.90	2.04	
L	0.30	0.43	0.55	
L1	0.35	0.54	0.69	
Ηe	2.10	2.40	2.64	
Т	0°		10°	

NOTES:

DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: 1.

2. MILLIMETERS.

MILLIME IERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE 3.

BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, 4. PROTRUSIONS, OR GATE BURRS.

#### RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **STYLES ON PAGE 2**

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#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CÁSE 318** ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	I	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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